Terminology

Term		Symbol	Description
Input	LED forward current	I_F	Current that flows between the input terminals when the input diode is forward biased.
	LED reverse voltage	V_R	Reverse breakdown voltage between the input terminals.
	Peak forward current	I_{FP}	Maximum instantaneous value of the forward current.
	LED operate current	I_{FON}	Current when the output switches on (by increasing the LED current) with a designated supply voltage and load connected between the output terminals.
	LED turn off current	I_{Foff}	Current when the output switches off (by decreasing the LED current) after operating the relay with a designated supply voltage and load connected between the output terminals.
	LED dropout voltage	V_F	Dropout voltage between the input terminals due to forward current.
	Power dissipation	P_{in}	Allowable power dissipation between the input terminals.
Output	Load voltage	V_L	Supply voltage range at the output used to normally operate the PhotoMOS relay. Represents the peak value for AC voltages.
	Continuous load current	I_L	Maximum current value that flows continuously between the output terminals of the PhotoMOS relay under designated ambient temperature conditions. Represents the peak value for AC current.
	On resistance	R_{on}	Obtained using the equation below from dropout voltage VDS (on) between the output terminals (when a designated LED current is made to flow through the input terminals and the designated load current through the output terminals.) $R_{on} = V_{DS}$ (on)/I_L
	Off state leakage current	I_{leak}	Current flowing to the output when a designated supply voltage is applied between the output terminals with no LED current flow.
	Power dissipation	P_{out}	Allowable power dissipation between the output terminals.
Electrical characteristics	Turn on time	T_{on}	Delay time until the output switches on after a designated LED current is made to flow through the input terminals.
	Turn off time	T_{off}	Delay time until the output switches off after the designated LED current flowing through the input terminals is cut off.
	I/O capacitance	C_{iso}	Capacitance between the input and output terminals.
	Output capacitance	C_{out}	Capacitance between output terminals when LED current does not flow.
	I/O isolation resistance	R_{iso}	Resistance between terminals (input and output) when a specified voltage is applied between the input and output terminals.
	Total power dissipation	P_T	Allowable power dissipation in the entire circuit between the input and output terminals.
	I/O isolation voltage	V_{iso}	Critical value before dielectric breakdown occurs, when a high voltage is applied for 1 minute between the same terminals where the I/O isolation resistance is measured.
	Operating temperature	T_{opr}	Ambient temperature range in which the PhotoMOS relay can operate normally with a designated load current conditions.
	Storage temperature	T_{stg}	Ambient temperature range in which the PhotoMOS relay can be stored without applying voltage.

Reliability tests

Classification	Item	Condition	Purpose
Life tests	High temperature storage test	T_{stg} (Max.)	Determines resistance to long term storage at high temperature.
	Low temperature storage test	T_{stg} (Min.)	Determines resistance to long term storage at low temperature.
	High temperature and high humidity storage test	85°C 185°F, R.H. 85%	Determines resistance to long term storage at high temperature and high humidity.
	Continuous operation life test	V_L = Max., I_L = Max., I_F = LED operate current (Max.)	Determines resistance to electrical stress (voltage and current).
Thermal environment tests	Temperature cycling test	Low storage temperature (T_{stg} Min.) High storage temperature (T_{stg} Max.)	Determines resistance to exposure to both low temperatures and high temperatures.
	Thermal shock test	Low temperature (0°C) (32°F), High temperature (100°C) (212°F)	Determines resistance to exposure to sudden changes in temperature.
	Solder burning resistance	260±5°C 500±41°F, 10 s	Determines resistance to thermal stress occurring while soldering.
Mechanical environment tests	Vibration test	196 m/s² {20 G}, 20 to 2,000 Hz*1	Determines the resistance to vibration sustained during shipment or operation.
	Shock test	9,800 m/s² {1,000 G} 0.5 ms*2; 4,900 m/s² {500 G} 1 ms	Determines the mechanical and structural resistance to shock.
	Drop test	Dropped at a height of 80 cm on oak board	Determines the mechanical resistance to drops sustained during shipment or operation.
	Terminal strength test	Determined from terminal shape and cross section	Determines the resistance to external force on the terminals of the PhotoMOS relay mounted on the PC board while wiring or operating.
	Solderability	230°C 446°F 5 s (with soldering flux)	Evaluates the solderability of the terminals.

*1 10 to 55 Hz at double amplitude of 3 mm for Power PhotoMOS relays.
*2 4,900 m/s², 1 ms for Power PhotoMOS relays.